

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (currently amended) A process for coating a substrate, ~~wherein~~ comprising:
applying a suspension of crystalline oxide particles in a suspending medium having a mean particle size from 0.5 to 9.9 nm ~~is applied~~ to a substrate to form a coating,
evaporating the suspending medium ~~is evaporated~~ and
sintering said the coating on the substrate ~~is sintered~~.
2. (currently amended) A process for coating a substrate as claimed in claim 1, wherein oxide particles having a mean particle size of from ~~0.5 to 9.9~~ 0.6 to 9 nm are used.
3. (previously presented) A process for coating a substrate as claimed in claim 1, wherein the oxide particles are BaTiO_3 , SrTiO_3 , $\text{Ba}_x\text{Sr}_{1-x}\text{TiO}_3$ where $x=0.01$ to 0.99 , $\text{Pb}(\text{Zr}_x\text{Ti}_{1-x})\text{O}_3$ where $x=0.01$ to 0.99 , $\text{Bi}_{4-x}\text{La}_x\text{Ti}_3\text{O}_{12}$ where $x=0$ to 4 or $\text{SrBi}_2\text{Ta}_2\text{O}_9$.
4. (previously presented) A process for coating a substrate as claimed in claim 1, wherein the suspending medium is an alcohol or a glycol ether.
5. (new) The process of claim 1, wherein said applying is by a process selected from the group consisting of spraying on or by spin-on.
6. (new) The process of claim 1, wherein said sintering is at a temperature below 1350°C .

7. (new) The process of claim 1, wherein oxide particles having a mean particle size of from 1 to 8 nm are used.

8. (new) The process of claim 1, wherein said substrate is a structured silicon wafer.

9. (new) The process of claim 1, wherein said suspension has a solids content of 1 to 35 wt. %.

10. (new) The process of claim 1, wherein said suspension has a solids content of 5 to 25 wt. %.